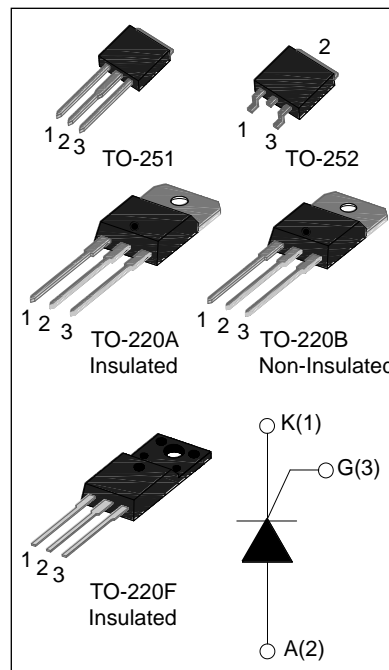




### DESCRIPTION:

JCT610/810 series of silicon controlled rectifiers, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc.

JCTx10A provides insulation voltage rated at 2500V RMS and JCTx10F provides insulation voltage rated at 2000V RMS from all three terminals to external heatsink. JCTx10A/JCTx10F series comply with UL standards (File ref: E252906).



### MAIN FEATURES

Symbol	JCT610	JCT810
$V_{DRM}/V_{RRM}$	600V	800V
$I_{T(RMS)}$	10A	
$I_{GT}$	$\leq 10mA$	

### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	$^{\circ}C$
Operating junction temperature range	$T_j$	-40-125	$^{\circ}C$
Repetitive peak off-state voltage( $T_j=25^{\circ}C$ )	$V_{DRM}$	600/800	V
Repetitive peak reverse voltage( $T_j=25^{\circ}C$ )	$V_{RRM}$	600/800	V
Non repetitive surge peak Off-state voltage	$V_{DSM}$	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage	$V_{RSM}$	$V_{RRM} + 100$	V
RMS on-state current	TO-251/ TO-252 ( $T_C=105^{\circ}C$ )	10	A
	TO-220B(Non-Ins) ( $T_C=110^{\circ}C$ )		

RMS on-state current	TO-220A(Ins) / TO-220F(Ins) ( $T_C=85^\circ\text{C}$ )	$I_{T(RMS)}$	10	A
Non repetitive surge peak on-state current ( $t_p=10\text{ms}$ )		$I_{TSM}$	120	A
$I^2t$ value for fusing ( $t_p=10\text{ms}$ )		$I^2t$	72	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ )		$di/dt$	50	$\text{A}/\mu\text{s}$
Peak gate current		$I_{GM}$	4	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power		$P_{GM}$	5	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	-	-	10	mA
$V_{GT}$		-	-	1.5	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	0.2	-	-	V
$I_L$	$I_G=1.2I_{GT}$	-	-	25	mA
$I_H$	$I_T=500\text{mA}$	-	-	15	mA
$dV/dt$	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$	50	-	-	$\text{V}/\mu\text{s}$

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=20\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.55	V
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	1	mA

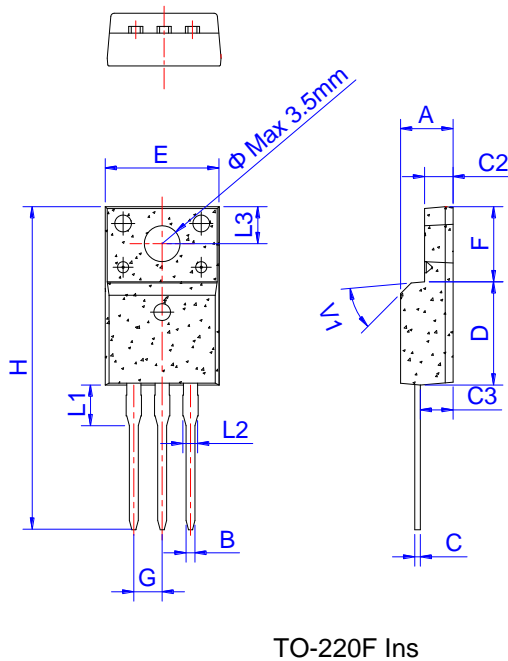
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)/ TO-220F(Ins)	4.8
		TO-220B(Non-Ins)	1.2
		TO-251/ TO-252	2.5

**ORDERING INFORMATION**

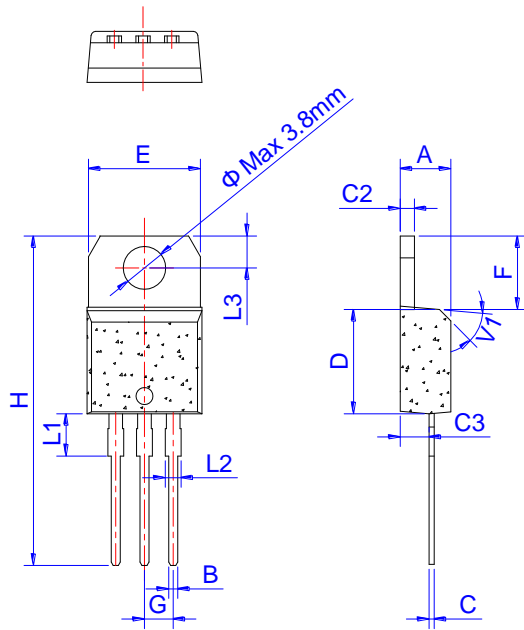
<p><b>J</b></p> <p>JieJie Microelectronics Co.,Ltd</p>	<p><b>CT</b></p> <p>SCRs</p> <p>6: <math>V_{DRM}/V_{RRM} \geq 600V</math> 8: <math>V_{DRM}/V_{RRM} &gt; 800V</math></p>	<p><b>6</b></p>	<p><b>10</b></p> <p><math>I_{T(RMS)}: 10A</math></p>	<p><b>B</b></p> <p>A: TO-220A(Ins) F: TO-220F(Ins) B: TO-220B(Non-Ins) H: TO-251 K: TO-252</p>
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**PACKAGE MECHANICAL DATA**



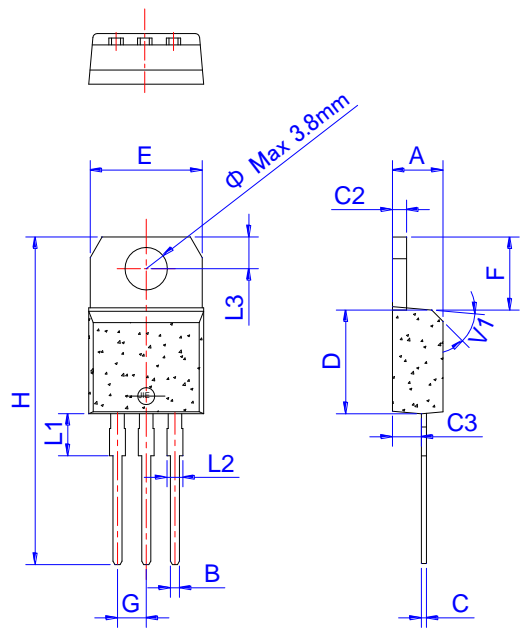
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.48		0.75	0.019		0.030
C2	2.40		2.70	0.094		0.106
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.70		10.3	0.382		0.406
F	6.40		7.00	0.252		0.276
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

PACKAGE MECHANICAL DATA



TO-220A Ins

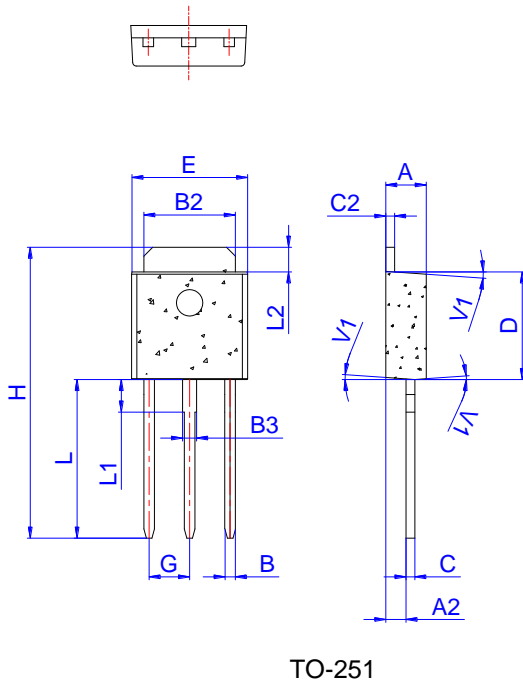
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



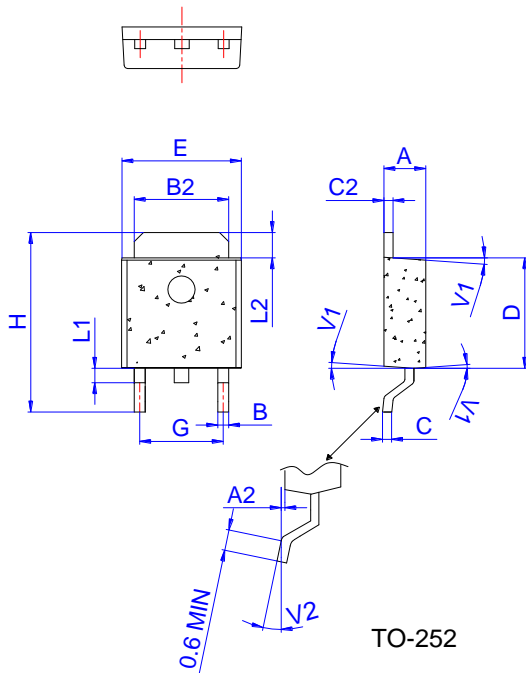
TO-220B Non-Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA

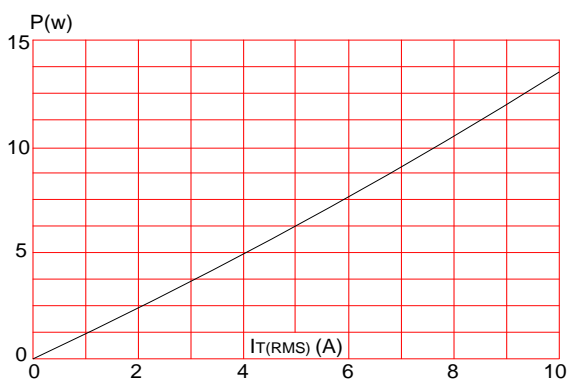


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	

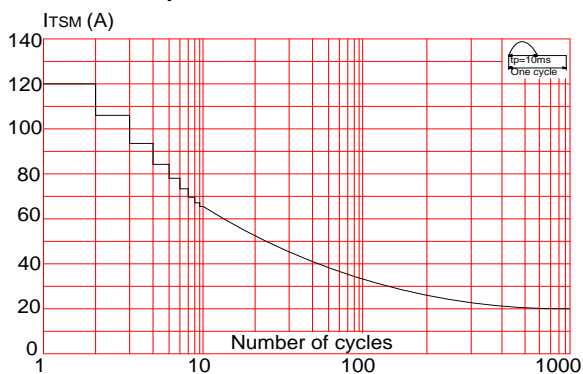


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2		0°	8°		0°	8°

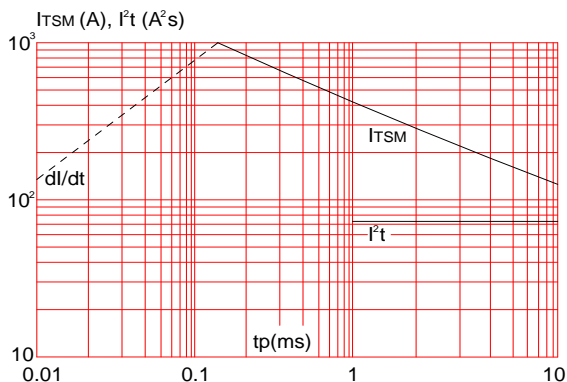
**FIG.1** Maximum power dissipation versus RMS on-state current



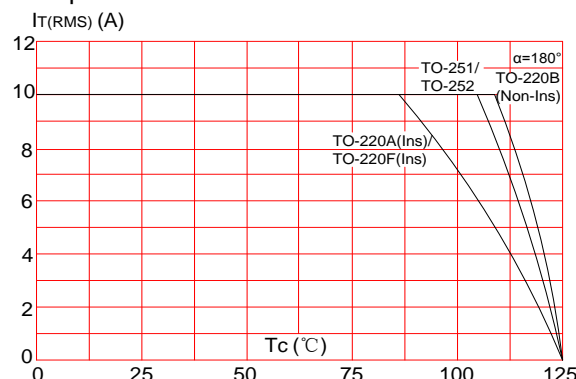
**FIG.3:** Surge peak on-state current versus number of cycles



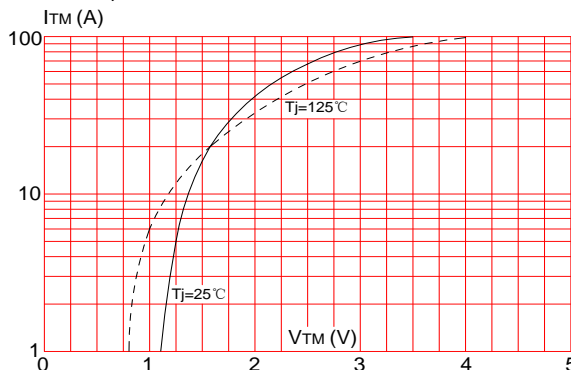
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )



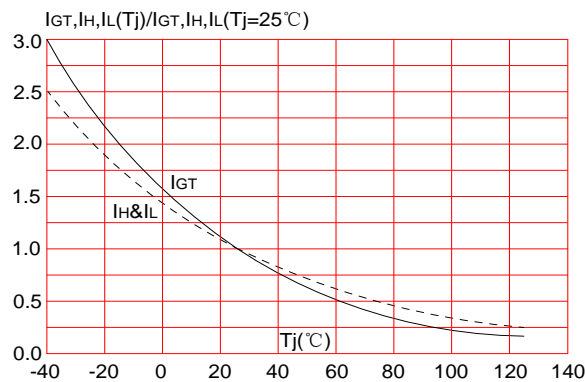
**FIG.2:** RMS on-state current versus case temperature




**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



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